

UNISONIC TECHNOLOGIES CO., LTD

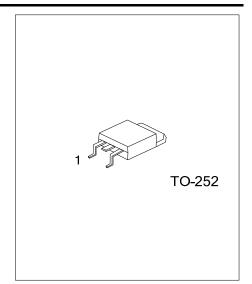
UTT25N08 Preliminary Power MOSFET

25A, 80V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **UTT25N08** is an N-channel enhancement mode power MOSFET using UTC's advanced technology to provide the customers with a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

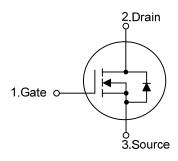
The UTC **UTT25N08** is universally applied in low voltage, such as automotive, high efficiency switching for DC/DC converters, and DC motor control.



■ FEATURES

- * $R_{DS(ON)}$ <0.12 Ω @ V_{GS} = 10 V
- * Typically 32pF low C_{RSS}
- * High switching speed
- * Typically 19nC low gate charge

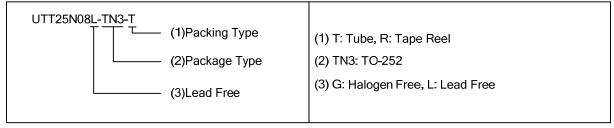
SYMBOL



■ ORDERING INFORMATION

Ordering	Doolsons	Pin Assignment			Daaldaa		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT25N08L-TN3-R	UTT25N08G-TN3-R	TO-252	G	D	S	Tape Reel	
UTT25N08L-TN3-T	UTT25N08G-TN3-T	TO-252	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ **ABSOLUTE MAXIMUM RATINGS** (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±25	V
Drain Current	Continuous	I _D	25	Α
	Pulsed	I _{DM}	100	Α
Power Dissipation		P _D	50	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	100	°C/W	
Junction to Case	θ _{JC}	2.5	°C/W	

■ **ELECTRICAL CHARACTERISTICS** (T_J = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I _D =250μA, V _{GS} =0V	80			V
Drain-Source Leakage Current		I_{DSS}	V _{DS} =80V, V _{GS} =0V			1	μΑ
Gate- Source Leakage Current	Forward	I _{GSS}	V_{GS} =+25V, V_{DS} =0V			+100	nA
	Reverse		V _{GS} =-25V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS	ON CHARACTERISTICS						
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =25A			120	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}			600	780	pF
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		165	215	pF
Reverse Transfer Capacitance		C_{RSS}			32	40	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V _{GS} =10V, V _{DS} =80V, I _D =25A (Note 1, 2)		19	25	nC
Gate to Source Charge		Q_GS			3.9		nC
Gate to Drain Charge		Q_GD	(Note 1, 2)		9.0		nC
Turn-ON Delay Time		$t_{D(ON)}$			7.5	25	ns
Rise Time		t_R	V_{DD} =50V, I_{D} =25A, R_{L} =50 Ω ,		150	310	ns
Turn-OFF Delay Time		t _{D(OFF)}	V _{GS} =10V, R _G =25Ω (Note 1, 2)		20	50	ns
Fall-Time		t_{F}			65	140	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				25	Α
Maximum Body-Diode Pulsed Current		I _{SM}				100	Α
Drain-Source Diode Forward Voltage		V_{SD}	I _S =25A, V _{GS} =0V			1.5	V

Notes: 1. Pulse Test: Pulse width≤300µs, Duty cycle≤2%

2. Essentially independent of operating temperature

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